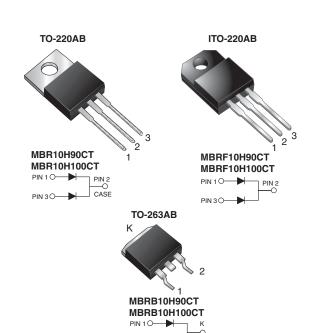
MBR(F,B)10H90CT, MBR(F,B)10H100CT

Vishay General Semiconductor

RoHS

Dual Common Cathode High Voltage Schottky Rectifier

High Barrier Technology for Improved High Temperature Performance



PRIMARY CHARACTERISTICS						
I _{F(AV)}	5 A x 2					
V _{RRM}	90 V, 100 V					
I _{FSM}	150 A					
V _F	0.61 V					
I _R	3.5 µA					
T _J max.	175 °C					

HEATSINK

FEATURES

- · Guardring for overvoltage protection
- · Low power loss, high efficiency
- Low forward voltage drop
- · Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB and ITO-220AB package)
- AEC-Q101 qualified
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters, and polarity protection application.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB

Molding compound meets UL 94-V-0 flammability rating Base P/N-E3 - RoHS-compliant, commercial grade Base P/NHE3 - RoHS-compliant, AEC-Q101 qualified

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test, HE3 suffix

meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T _C = 25 °C unless otherwise noted)						
PARAMETER		SYMBOL	MBR10H90CT	MBR10H100CT	UNIT	
Maximum repetitive peak reverse voltage	um repetitive peak reverse voltage		90	100		
Working peak reverse voltage		V_{RWM}	90	100	V	
Maximum DC blocking voltage		V_{DC}	90	100		
Maximum average forward rectified current at T _C = 105 °C	total device	_	10			
	per diode	I _{F(AV)}	5.0			
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		I _{FSM}	150		A	
Peak repetitive reverse current per diode at $t_p = 2.0 \mu s$, 1 kHz		I _{RRM}	0.5			
Voltage rate of change (rated V _R)		dV/dt	10 000		V/µs	
Operating junction and storage temperature range		T _J , T _{STG}	- 65 to 175		°C	
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min		V _{AC}	1500		V	



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ELECTRICAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUE	UNIT		
Maximum instantaneous forward voltage per diode	V _F ⁽¹⁾	I _F = 5 A	T _J = 25 °C	0.76	V		
		I _F = 5 A	T _J = 125 °C	0.61			
		I _F = 10 A	T _J = 25 °C	0.85			
		I _F = 10 A	T _J = 125 °C	0.71			
Maximum reverse current per diode	I _R ⁽¹⁾	Rated V _R	T _J = 25 °C	3.5	μΑ		
Maximum reverse current per diode			T _J = 100 °C	4.5	mA		

Notes

 $^{(1)}$ Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width \leq 40 ms

THERMAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	MBR	MBRF	MBRB	UNIT
Typical thermal resistance per diode	$R_{ heta JC}$	2.2	5.2	2.2	°C/W

ORDERING INFORMATION (Example)							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
TO-220AB	MBR10H100CT-E3/45	1.85	45	50/tube	Tube		
ITO-220AB	MBRF10H100CT-E3/45	1.79	45	50/tube	Tube		
TO-263AB	MBRB10H100CT-E3/45	1.35	45	50/tube	Tube		
TO-263AB	MBRB10H100CT-E3/81	1.35	81	800/reel	Tape and reel		
TO-220AB	MBR10H100CTHE3/45 (1)	1.85	45	50/tube	Tube		
ITO-220AB	MBRF10H100CTHE3/45 (1)	1.79	45	50/tube	Tube		
TO-263AB	MBRB10H100CTHE3/45 (1)	1.35	45	50/tube	Tube		
TO-263AB	MBRB10H100CTHE3/81 (1)	1.35	81	800/reel	Tape and reel		

Note

(1) AEC-Q101 qualified

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RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

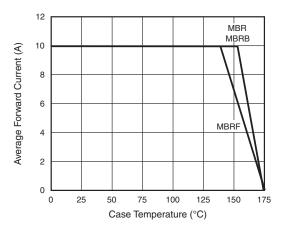


Fig. 1 - Forward Current Derating Curve Per Diode

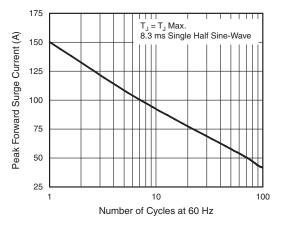


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

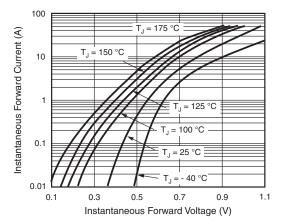


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

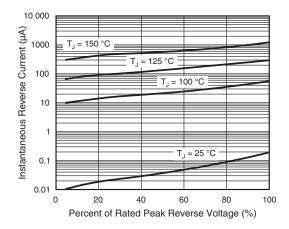


Fig. 4 - Typical Reverse Characteristics Per Diode

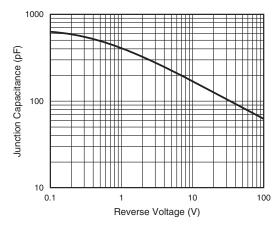


Fig. 5 - Typical Junction Capacitance Per Diode

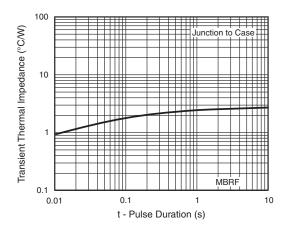


Fig. 6 - Typical Transient Thermal Impedance Per Diode



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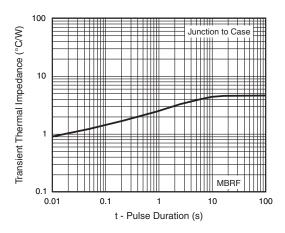
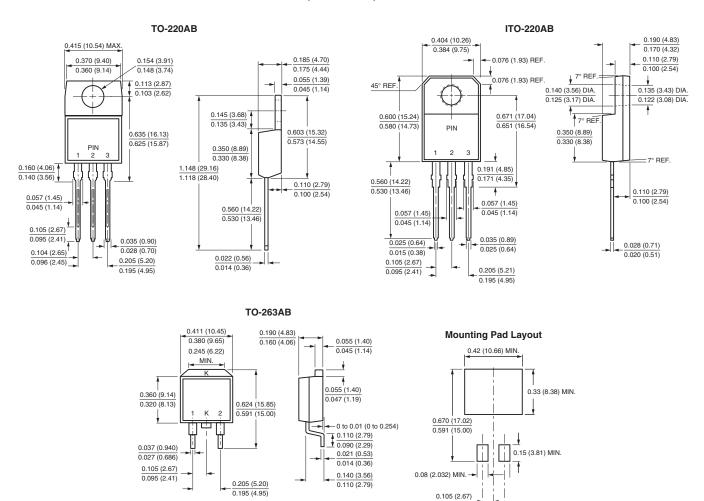


Fig. 7 - Typical Transient Thermal Impedance Per Diode

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



0.095 (2.41)



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